



DMN2055U

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
201/	$38m\Omega$ @ $V_{GS} = 4.5V$	4.8A
20V	$45m\Omega @ V_{GS} = 2.5V$	4.5A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- General Purpose Interfacing Switch
- Power Management Functions

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

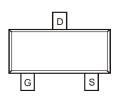
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)

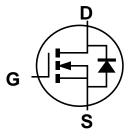
SOT23







Top View



Equivalent Circuit

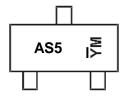
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2055U-7	SOT23	3,000/Tape & Reel
DMN2055U-13	SOT23	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



Date Code Key

Year	2017	2018	20	019	2020	2021		2022	2023	202	24	2025
Code	Е	F		G	Н			J	K	L		М
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

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Maximum Ratings $(@T_A = +25^{\circ}C, \text{ unless otherwise specified.})$

Characte	eristic		Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage		V _{GSS}	±8	V	
Continuous Drain Current (Note 6) Steady $T_A = +25^{\circ}\text{C}$ State $T_A = +85^{\circ}\text{C}$			I _D	4.8 3.8	А
Pulsed Drain Current (10µs Pulse, Dut	y Cycle = 1%)		I _{DM}	25	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

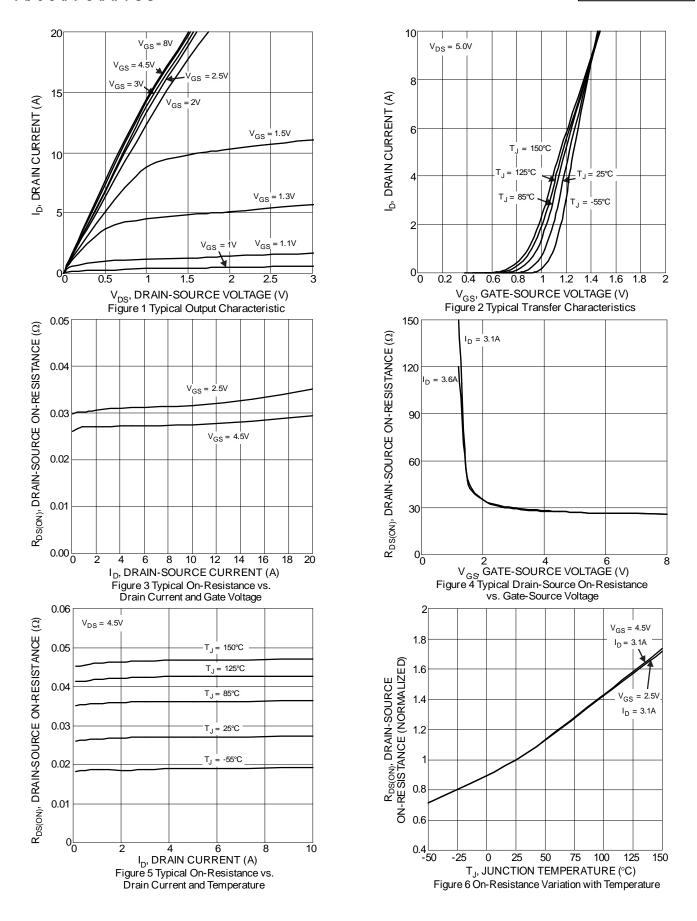
Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		P_D	0.8	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	162	°C/W	
Total Power Dissipation (Note 6)	•	P _D	1.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	113	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

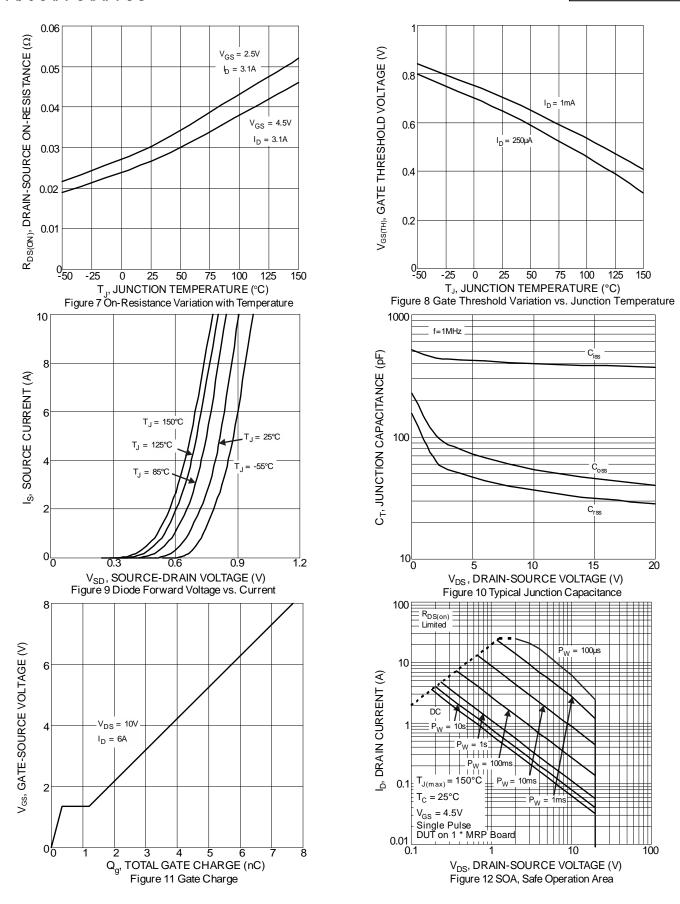
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 7)								
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$		
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	1.0	μA	V _{DS} = 20V, V _{GS} = 0V		
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$		
ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage	V _{GS(TH)}	0.4	_	1.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$		
Static Drain-Source On-Resistance	5		28	38	mΩ	$V_{GS} = 4.5V, I_D = 3.6A$		
Static Dialif-Source Off-Resistance	R _{DS(ON)}	_	32	45	11122	$V_{GS} = 2.5V, I_D = 3.1A$		
Diode Forward Voltage	V_{SD}	_	0.7	1.0	V	$V_{GS} = 0V, I_{S} = 1A$		
DYNAMIC CHARACTERISTICS (Note 8)	DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}		400	_	pF			
Output Capacitance	Coss	_	55	_	pF	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz		
Reverse Transfer Capacitance	C _{rss}	_	37	_	pF	1 = 1.000112		
Gate Resistance	R_{G}	_	3.7	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$		
Total Gate Charge	Q_{G}	_	4.3	_	nC			
Gate-Source Charge	Q _{GS}	_	0.3	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$		
Gate-Drain Charge	Q_{GD}	_	4.8	_	nC	$I_D = 6A$		
Turn-On Delay Time	t _{D(ON)}	_	2.8	_	ns			
Turn-On Rise Time	t _R		2.7	_	ns	$V_{DD} = 10V, V_{GS} = 5V,$		
Turn-Off Delay Time	t _{D(OFF)}		15.4	_	ns	$R_L = 1.7\Omega$, $R_G = 6\Omega$		
Turn-Off Fall Time	t _F		4.4	_	ns	1		
Reverse Recovery Time	t _{RR}	1	6.8	-	ns	$I_F = 1.0A$, $di/dt = 100A/\mu s$		
Reverse Recovery Charge	Q _{RR}		1.2	_	nC	$I_F = 1.0A$, $di/dt = 100A/\mu s$		

 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing. Notes:

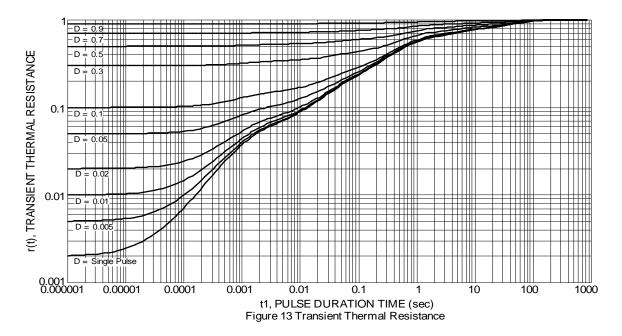










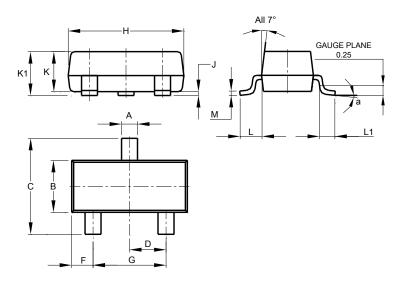




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

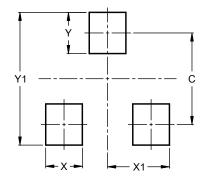


SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
7	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
١	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°					
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)				
С	2.0				
Х	0.8				
X1	1.35				
Y	0.9				
V1	2.0				



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